

	Typ	L #	Hits	Search T xt	DBs	Time Stamp
1	BRS	L1	9553	("GaAs" near5 (layer or film))	USPAT ; US-PG	2003/09/19 11:22
2	BRS	L2	2148	("InGaAsP" near5 (layer or film))	USPAT ; US-PG	2003/09/19 11:19
3	BRS	L3	1813	(etching or etched or etches or etch) near15 ((peroxide or "h.sub.2 o.sub.2") near6 (water or "h.sub.2 o"))	USPAT ; US-PG	2003/09/19 11:26
4	BRS	L4	204	1 same 2	USPAT ; US-PG	2003/09/19 11:27
5	BRS	L5	2	3 same 4	USPAT ; US-PG	2003/09/19 11:11
6	BRS	L8	1926	(etching or etched or etches or etch) near15 ((peroxide or "h.sub.2 o.sub.2") near15 (water or "h.sub.2 o"))	USPAT ; US-PG	2003/09/19 11:13
7	BRS	L9	2	4 same 8	USPAT ; US-PG	2003/09/19 11:13
8	BRS	L10	42	(etching or etched or etches or etch) same 4	USPAT ; US-PG	2003/09/19 11:14
9	BRS	L11	4751	(etching or etched or etches or etch) near15 (peroxide or "h.sub.2 o.sub.2")	USPAT ; US-PG	2003/09/19 11:16
10	BRS	L12	3	11 same 4	USPAT ; US-PG	2003/09/19 11:16
11	BRS	L13	15109	("GaAs" near5 (layer or film))	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:20
12	BRS	L14	2646	("InGaAsP" near5 (layer or film))	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:19
13	BRS	L15	331	(etching or etched or etches or etch) near15 ((peroxide or "h.sub.2 o.sub.2") near6 (water or "h.sub.2 o"))	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:21
14	BRS	L16	91	13 and 14	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:19

	Typ	L #	Hits	Search T xt	DBs	Time Stamp
15	BRS	L17	0	16 and 15	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:19
16	BRS	L18	235	"GaAs" same "InGaAsP"	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:21
17	BRS	L19	0	15 and 18	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:21
18	BRS	L20	1236	(etching or etched or etches or etch) near15 (peroxide or "h.sub.2 o.sub.2")	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:21
19	BRS	L21	2	18 and 20	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:21
20	BRS	L22	1671	"GaAs" same "InGaAsP"	USPAT ; US-PG	2003/09/19 11:22
21	BRS	L23	9	3 same 22	USPAT ; US-PG	2003/09/19 11:22
22	BRS	L24	2148	1near15 2	USPAT ; US-PG	2003/09/19 11:27
23	BRS	L25	101	1 near15 2	USPAT ; US-PG	2003/09/19 11:27
24	BRS	L26	25	25 same (etched or etch or etching or etches)	USPAT ; US-PG	2003/09/19 11:29
25	BRS	L27	1146	(etched or etch or etching or etches) near5 ("h.sub.2 o.sub.2")	USPAT ; US-PG	2003/09/19 11:30
26	BRS	L28	2	25 same 27	USPAT ; US-PG	2003/09/19 11:30
27	BRS	L35	0	((("GaAs" near5 (layer or film))) same (("InGaAsP" near5 (layer or film)))) and ((etching or etched or etch) near15 (("h.sub.3po.sub.4" adj3 "hcl" adj3 "h.sub.2o") or ((citric adj2 acid) adj2 "h.sub.2 o.sub.2") or ("h.sub.3 p o.sub.4" adj2 "hcl"))))	USPAT ; US-PG PUB	2003/09/19 11:30

	Type	L #	Hits	Search T xt	DBs	Tim Stamp
28	BRS	L38	0	20030138984.URPN.	USPAT	2003/09/19 11:30
29	BRS	L29	8346	("GaAs" near3 (layer or film))	USPAT ; US-PG	2003/09/19 11:31
30	BRS	L30	9553	("GaAs" near5 (layer or film))	USPAT ; US-PG	2003/09/19 11:31
31	BRS	L31	2148	("InGaAsP" near5 (layer or film))	USPAT ; US-PG	2003/09/19 11:32
32	BRS	L32	204	((("GaAs" near5 (layer or film)))) same ((("InGaAsP" near5 (layer or film))))	USPAT ; US-PG	2003/09/19 11:32
33	BRS	L33	42	(etching or etched or etch) same (((("GaAs" near5 (layer or film)))) same ((("InGaAsP" near5 (layer or film))))	USPAT ; US-PG	2003/09/19 11:32
34	BRS	L34	13	(etching or etched or etch) near5 (("h.sub.3po.sub.4" adj3 "hcl" adj3 "h.sub.2o") or ((citric adj2 acid) adj2 "h.sub.2 o.sub.2") or ("h.sub.3 p o.sub.4" adj2 "hcl"))	USPAT ; US-PG PUB	2003/09/19 11:32
35	BRS	L36	17	(etching or etched or etch) near15 (("h.sub.3po.sub.4" adj3 "hcl" adj3 "h.sub.2o") or ((citric adj2 acid) adj2 "h.sub.2 o.sub.2") or ("h.sub.3 p o.sub.4" adj2 "hcl"))	USPAT ; US-PG PUB	2003/09/19 11:32
36	BRS	L37	5	"GaAs" near10 "InGaAsP" near10 interface	USPAT ; US-PG	2003/09/19 11:32
37	BRS	L39	15109	("GaAs" near5 (layer or film))	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:32
38	BRS	L40	2646	("InGaAsP" near5 (layer or film))	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:33
39	BRS	L41	91	((("GaAs" near5 (layer or film)))) and ((("InGaAsP" near5 (layer or film))))	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:33
40	BRS	L42	21	(etching or etched or etch) and (((("GaAs" near5 (layer or film)))) and ((("InGaAsP" near5 (layer or film))))	EPO; JPO; DERW ENT; IBM_T DB	2003/09/19 11:33
41	BRS	L43	1	controlling adj3 spatial adj3 mode	EPO; JPO; DERW ENT	2003/09/19 11:37

	Type	L #	Hits	Search Text	DBs	Tim Stamp
1	BRS	L1	28	GaAs/InGaP	USPAT ; US-PG	2003/09/19 12:46
2	BRS	L2	257	InGaP near5 (quantum or active)	USPAT ; US-PG	2003/09/19 12:47